Vincotech

A0-VS126PA150M7-L998F70

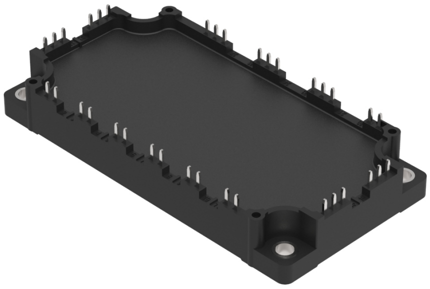
datasheet

VINcoPACK E3 **1200 V / 150 A**

Features

- IGBT Mitsubishi gen 7 technology with low VCesat and improved EMC behavior
- New SoLid Cover Technology for higher reliability
- Industry standard housing
- Press-fit pin and pre-applied phase-change Thermal Interface Material available

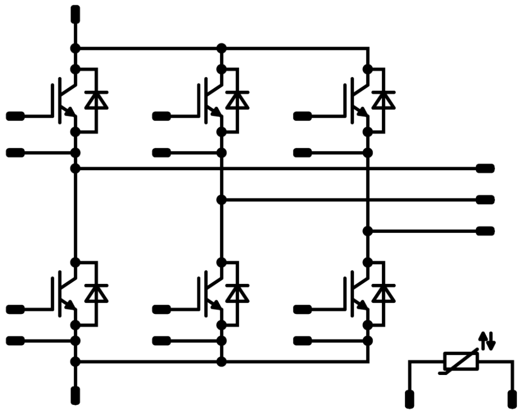
VINco E3 17 mm housing



Target applications

- Industrial Drives

Schematic



Types

- A0-VS126PA150M7-L998F70

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions		Value	Unit
Inverter Switch					
Collector-emitter voltage	V_{CES}			1200	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$	T_s = 80 °C	144	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}		300	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	272	W
Gate-emitter voltage	V_{GES}			±20	V
Short circuit ratings	t_{SC}	V_{GE} = 15 V, V_{CC} = 800 V	T_j = 150 °C	9,5	µs
Maximum junction temperature	T_{jmax}			175	°C
Inverter Diode					
Peak repetitive reverse voltage	V_{RRM}			1200	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	117	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		300	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	204	W
Maximum junction temperature	T_{jmax}			175	°C
Module Properties					
Thermal Properties					
Storage temperature	T_{stg}			-40…+125	°C
Operation temperature under switching condition	T_{jop}			-40…+(T_{jmax} - 25)	°C
Isolation Properties					
Isolation voltage	V_{isol}	DC Test Voltage*	t_p = 2 s	6000	V
Isolation voltage	V_{isol}	AC Voltage	t_p = 1 min	2500	V
Creepage distance				>12,7	mm
Clearance				9	mm
Comparative Tracking Index	CTI			≥ 200	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_{F} [V]	I_{C} [A] I_{D} [A] I_{F} [A]	T_{j} [°C]	Min	Typ	Max	
Inverter Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$			10	0,015	25	5,4	6	6,6	V
Collector-emitter saturation voltage	V_{CEsat}		15		150	25 125 150		1,58 1,8 1,86	1,85(1)	V
Collector-emitter cut-off current	I_{CES}		0	1200		25			100	µA
Gate-emitter leakage current	I_{GES}		20	0		25			500	nA
Internal gate resistance	r_{g}							3		Ω
Input capacitance	C_{ies}		0	10		25		30000		pF
Output capacitance	C_{oes}							880		pF
Reverse transfer capacitance	C_{res}							320		pF
Gate charge	Q_{g}	V_{CC} = 600 V	15		150	25		1000		nC
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,35		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 1 Ω R_{goff} = 1 Ω	±15	600	150	25 125 150		291,8 306,4 309,2		ns
Rise time	t_{r}					25 125 150		52,8 62,2 67		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		239,2 271,8 282,4		ns
Fall time	t_{f}					25 125 150		63,21 86,11 93,9		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=14,21 µC Q_{rFWD}=22,33 µC Q_{rFWD}=25,72 µC				25 125 150		14,9 20,53 22,36		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		8,75 12,22 13,26		mWs

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	Unit
Inverter Diode										
Static										
Forward voltage	V_F				150	25 125 150		1,79 1,9 1,9	2,1(1)	V
Reverse leakage current	I_R	V_r = 1200 V				25			40	µA
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,46		K/W
Dynamic										
Peak recovery current	I_{RRM}	d*i*/d*t*=2255 A/µs d*i*/d*t*=1996 A/µs d*i*/d*t*=1932 A/µs	±15	600	150	25 125 150		88,34 90,48 91,78		A
Reverse recovery time	t_{rr}					25 125 150		344,7 507 562,67		ns
Recovered charge	Q_r					25 125 150		14,21 22,33 25,72		µC
Reverse recovered energy	E_{rec}					25 125 150		4,94 8,13 9,46		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		452,88 328,17 325,43		A/µs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Thermistor										
Static										
Rated resistance	R					25		5		kΩ
Deviation of R_{100}	$\Delta_{R/R}$	R_{100} = 493 Ω				100	-5		5	%
Power dissipation	P							245		mW
Power dissipation constant	d					25		1,4		mW/K
B-value	$B_{(25/50)}$	Tol. ±2 %						3375		K
B-value	$B_{(25/100)}$	Tol. ±2 %						3437		K
Vincotech Thermistor Reference									K	

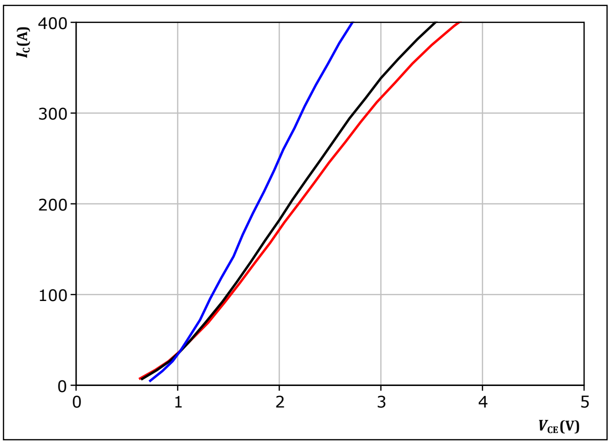
(1) Value at chip level
(2) Only valid with pre-applied Vincotech thermal interface material.

Inverter Switch Characteristics

figure 1. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$

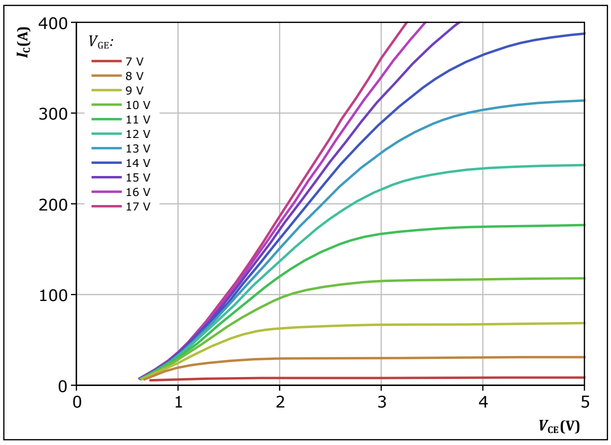


t_p =	250	μs		25 °C
V_{GE} =	15	V	T_j:	125 °C
				150 °C

figure 2. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$



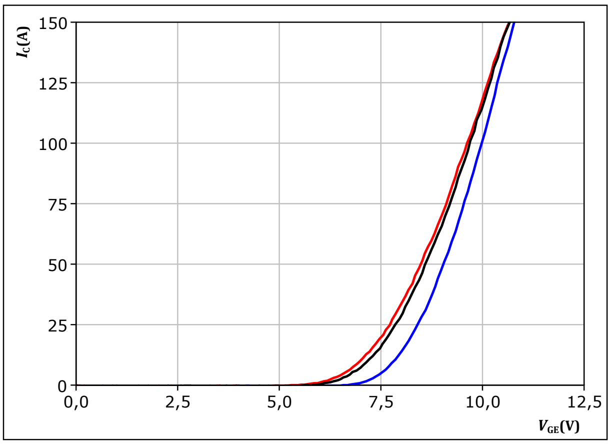
t_p =	250	μs
T_j =	150	°C

V_{GE} from 7 V to 17 V in steps of 1 V

figure 3. **IGBT**

Typical transfer characteristics

$I_C = f(V_{GE})$

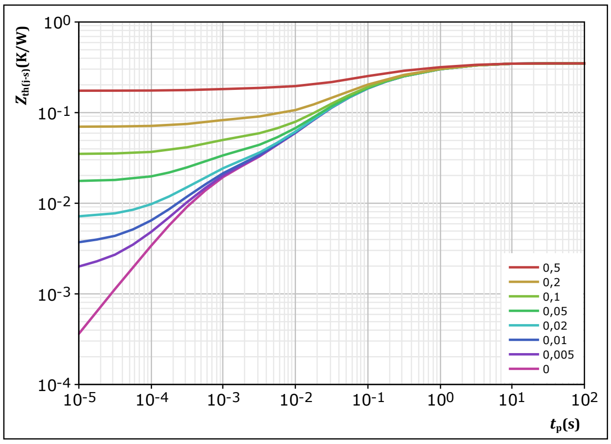


t_p =	250	μs		25 °C
V_{CE} =	10	V	T_j:	125 °C
				150 °C

figure 4. **IGBT**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D =	t_p / T	
$R_{th(j-s)}$ =	0,349	K/W

IGBT thermal model values

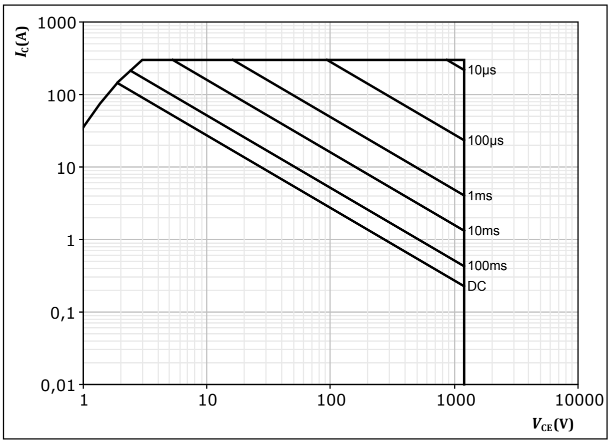
R (K/W)	τ (s)
4,14E-02	3,34E+00
8,71E-02	6,14E-01
1,12E-01	1,17E-01
8,40E-02	2,74E-02
8,14E-03	5,18E-03
1,66E-02	5,36E-04

Inverter Switch Characteristics

figure 5.	IGBT

Safe operating area

$I_C = f(V_{CE})$



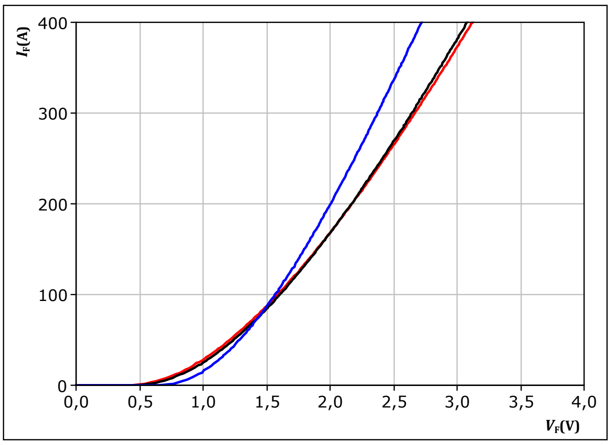
D =	single pulse	
T_s =	80	°C
V_{GE} =	15	V
T_j =	T_{jmax}	

Inverter Diode Characteristics

figure 6. **FWD**

Typical forward characteristics

$I_F = f(V_F)$



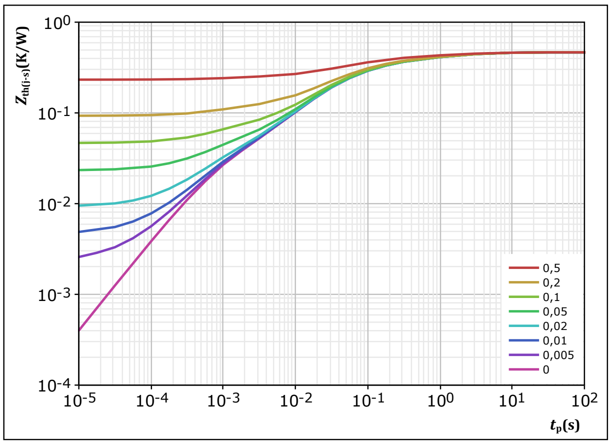
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 7. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



$D = t_p / T$

$R_{th(j-s)}$ = 0,465 K/W

FWD thermal model values

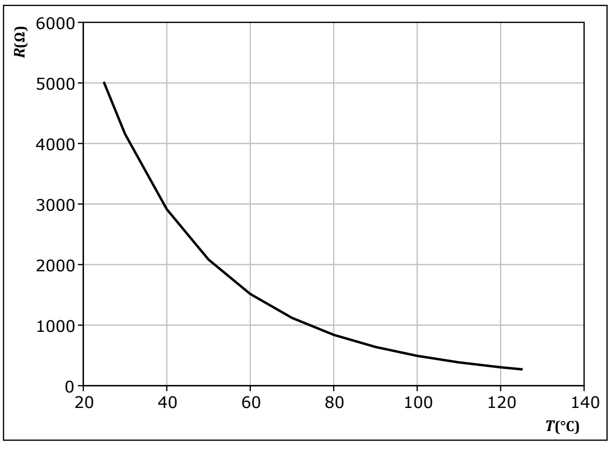
R (K/W)	τ (s)
3,22E-02	4,93E+00
6,91E-02	1,02E+00
1,24E-01	1,62E-01
1,47E-01	4,06E-02
6,91E-02	1,26E-02
2,40E-02	7,94E-04

Thermistor Characteristics

figure 8.	Thermistor

Typical NTC characteristic as function of temperature

R_T = f(T)

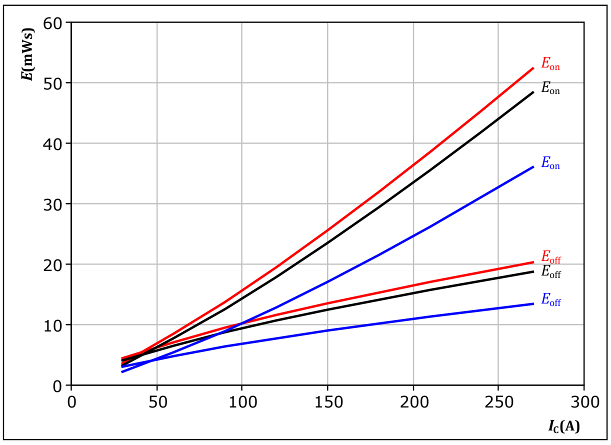


Inverter Switching Characteristics

figure 9. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



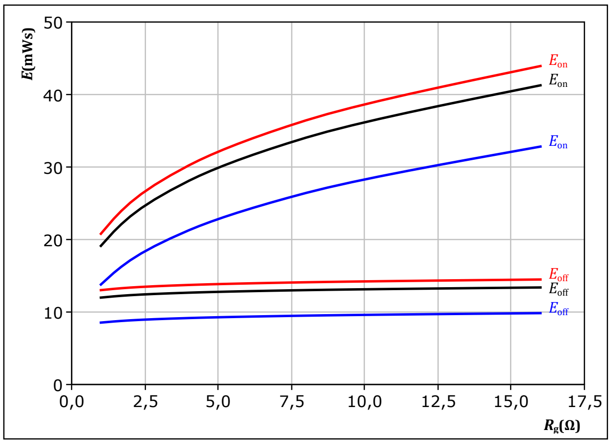
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	1	Ω		150 °C
R_{goff} =	1	Ω		

figure 10. **IGBT**

Typical switching energy losses as a function of gate resistor

$E = f(R_g)$



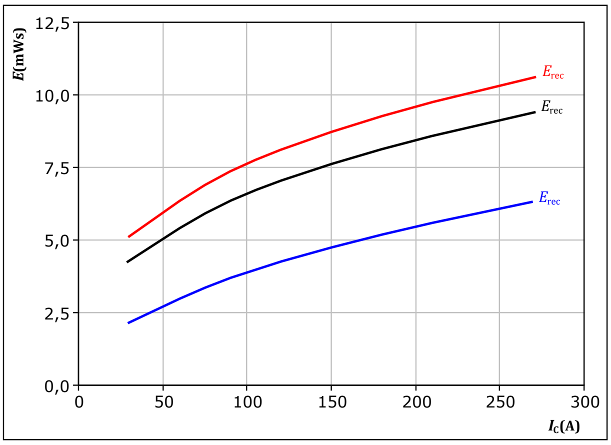
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	150	A		150 °C

figure 11. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_C)$



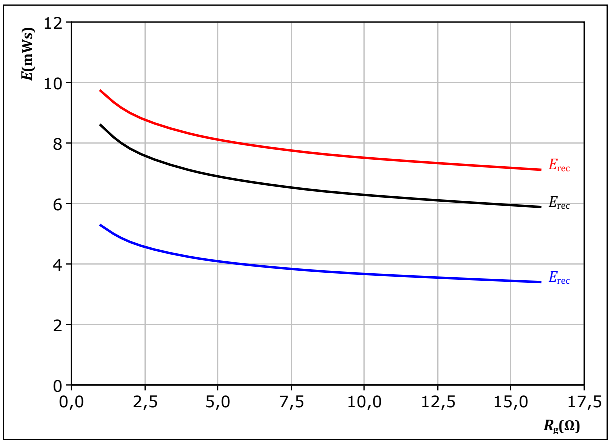
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	1	Ω		150 °C

figure 12. **FWD**

Typical reverse recovered energy loss as a function of gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

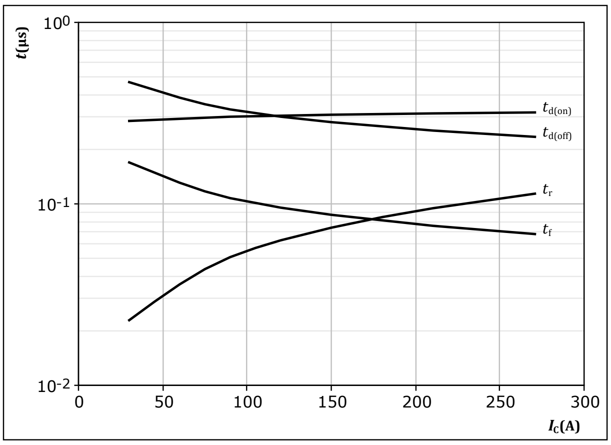
V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	150	A		150 °C

Inverter Switching Characteristics

figure 13. **IGBT**

Typical switching times as a function of collector current

$t = f(I_C)$



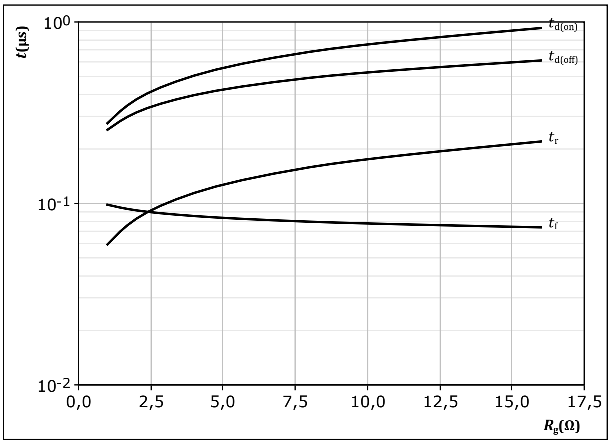
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	1	Ω
R_{goff} =	1	Ω

figure 14. **IGBT**

Typical switching times as a function of gate resistor

$t = f(R_g)$



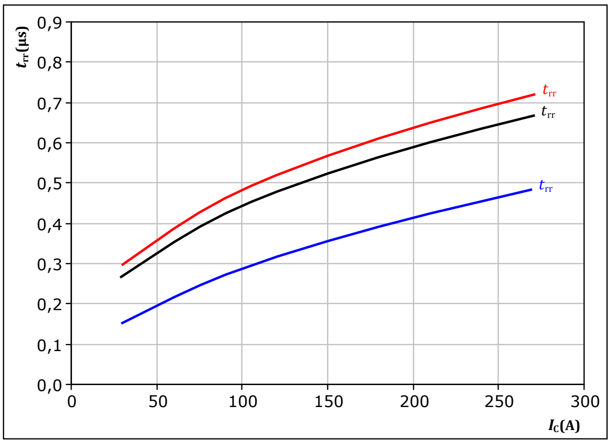
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	150	A

figure 15. **FWD**

Typical reverse recovery time as a function of collector current

$t_{rr} = f(I_C)$



With an inductive load at

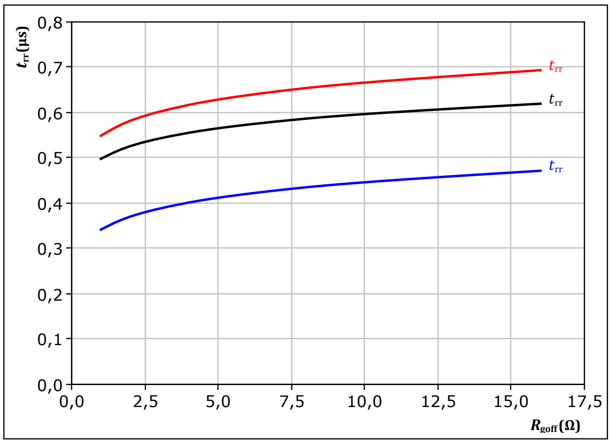
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	1	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 16. **FWD**

Typical reverse recovery time as a function of IGBT turn off gate resistor

$t_{rr} = f(R_{goff})$



With an inductive load at

V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	150	A

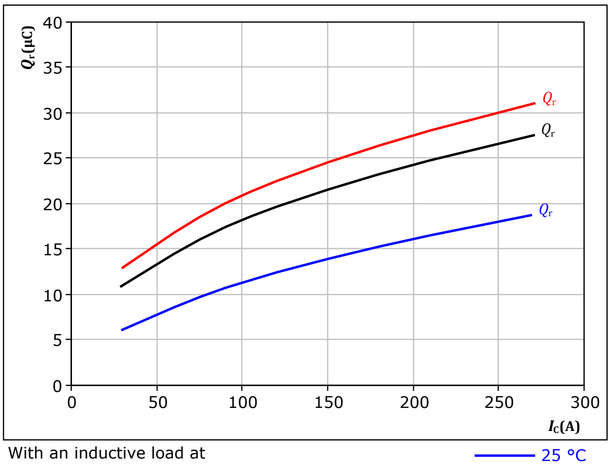
T_j: 25 °C, 125 °C, 150 °C

Inverter Switching Characteristics

figure 17. **FWD**

Typical recovered charge as a function of collector current

Q_r = f(I_C)



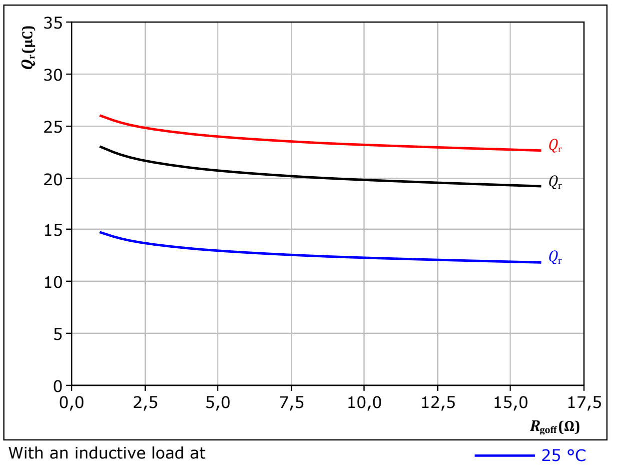
With an inductive load at

V_{CE} =	600	V	T_j: 25 °C / 125 °C / 150 °C
V_{GE} =	±15	V	
R_{gon} =	1	Ω	

figure 18. **FWD**

Typical recovered charge as a function of turn off gate resistor

Q_r = f(R_{goff})



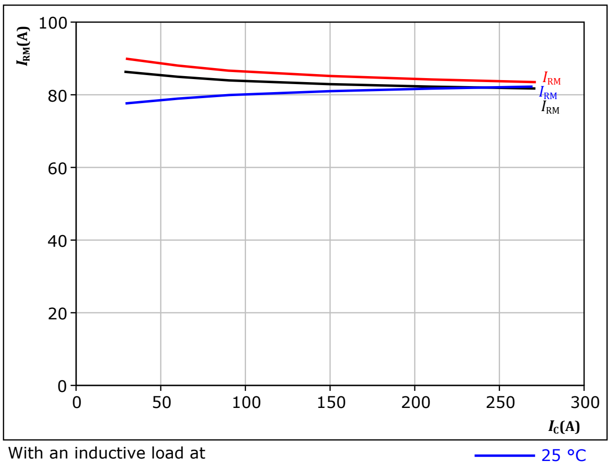
With an inductive load at

V_{CE} =	600	V	T_j: 25 °C / 125 °C / 150 °C
V_{GE} =	±15	V	
I_C =	150	A	

figure 19. **FWD**

Typical peak reverse recovery current as a function of collector current

I_{RM} = f(I_C)



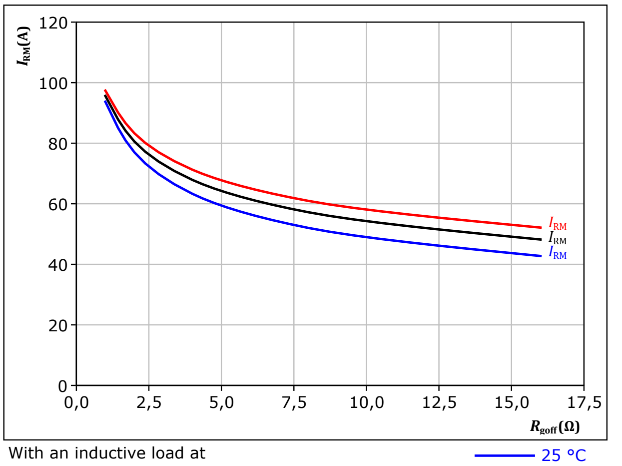
With an inductive load at

V_{CE} =	600	V	T_j: 25 °C / 125 °C / 150 °C
V_{GE} =	±15	V	
R_{gon} =	1	Ω	

figure 20. **FWD**

Typical peak reverse recovery current as a function of turn off gate resistor

I_{RM} = f(R_{goff})



With an inductive load at

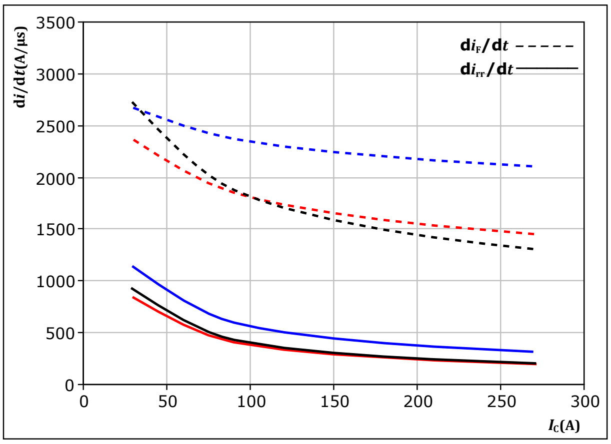
V_{CE} =	600	V	T_j: 25 °C / 125 °C / 150 °C
V_{GE} =	±15	V	
I_C =	150	A	

Inverter Switching Characteristics

figure 21. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, di_{rr}/dt = f(I_C)



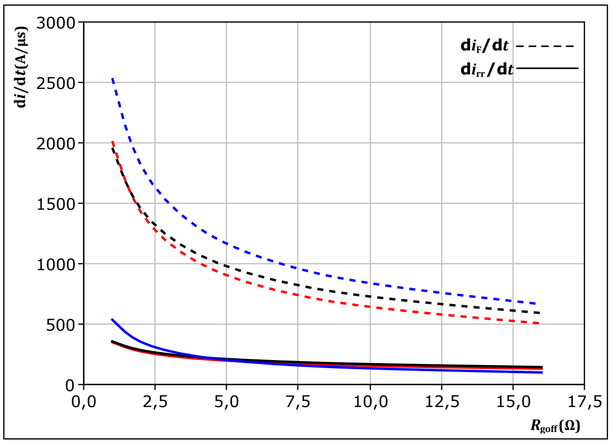
With an inductive load at

V_{CE} =	600	V	T_j: 25 °C / 125 °C / 150 °C
V_{GE} =	±15	V	
R_{gon} =	1	Ω	

figure 22. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of turn off gate resistor

di_F/dt, di_{rr}/dt = f(R_{goff})



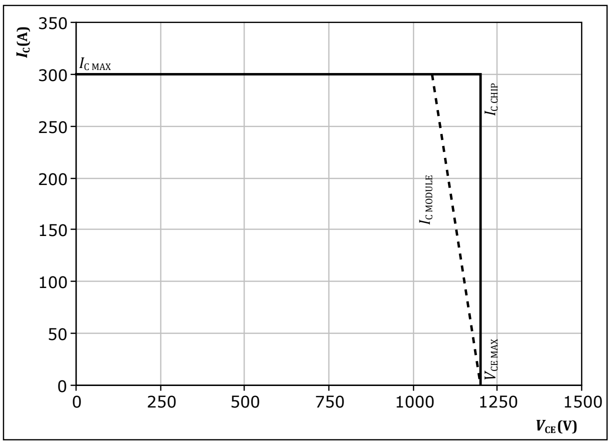
With an inductive load at

V_{CE} =	600	V	T_j: 25 °C / 125 °C / 150 °C
V_{GE} =	±15	V	
I_C =	150	A	

figure 23. **IGBT**

Reverse bias safe operating area

I_C = f(V_{CE})



At	T_j =	150	°C
	R_{gon} =	1	Ω
	R_{goff} =	1	Ω

Inverter Switching Definitions

figure 24.	IGBT

Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{tEoff} **= integrating time for** E_{off})

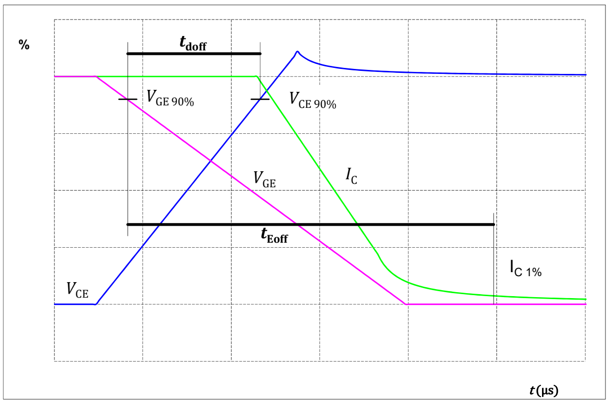


figure 25.	IGBT

Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} **= integrating time for** E_{on})

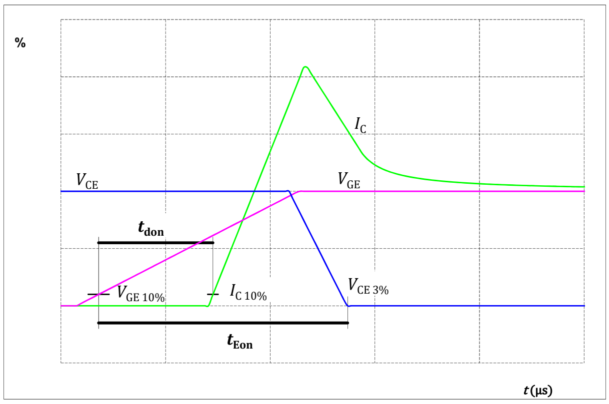


figure 26.	IGBT

Turn-off Switching Waveforms & definition of t_f

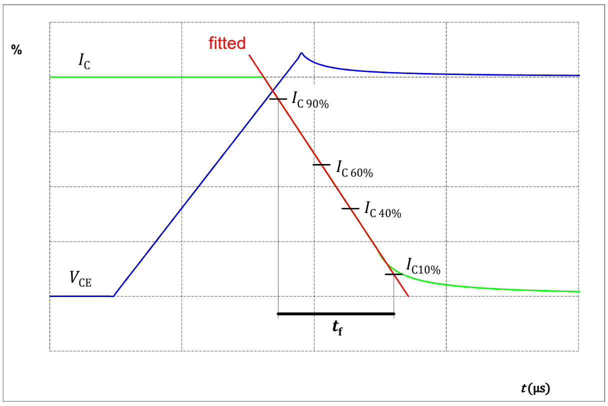
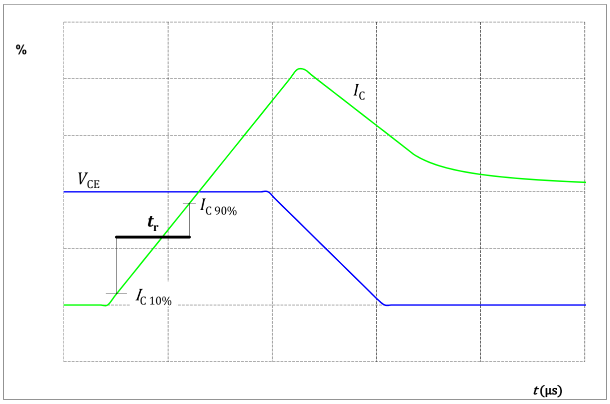


figure 27.	IGBT

Turn-on Switching Waveforms & definition of t_r



Inverter Switching Definitions

figure 28. **FWD**

Turn-off Switching Waveforms & definition of t_{rr}

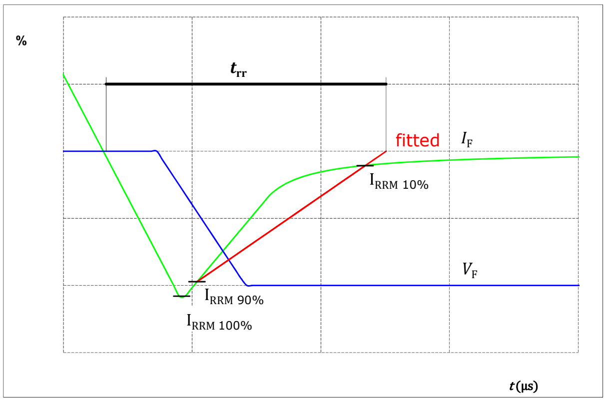
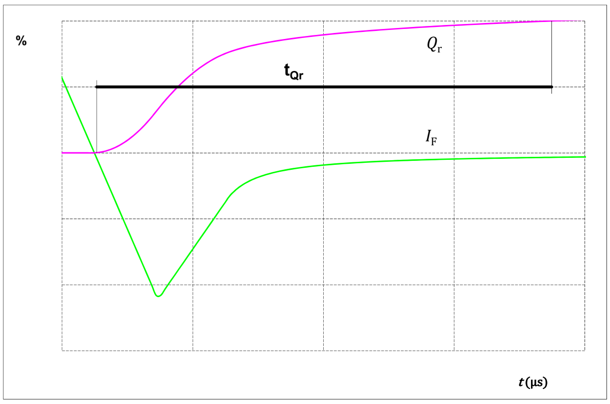


figure 29. **FWD**

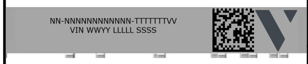
Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)



Ordering Code

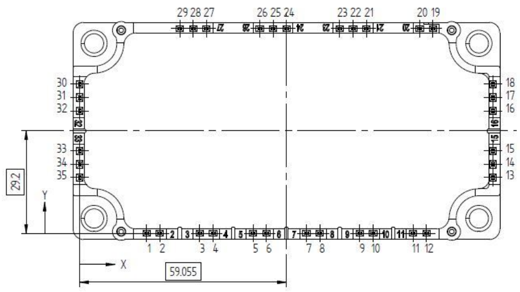
Version	Ordering Code
Without thermal paste	A0-VS126PA150M7-L998F70
With thermal paste (3,4 W/mK, PSX-P7)	A0-VS126PA150M7-L998F70-/3/

Marking

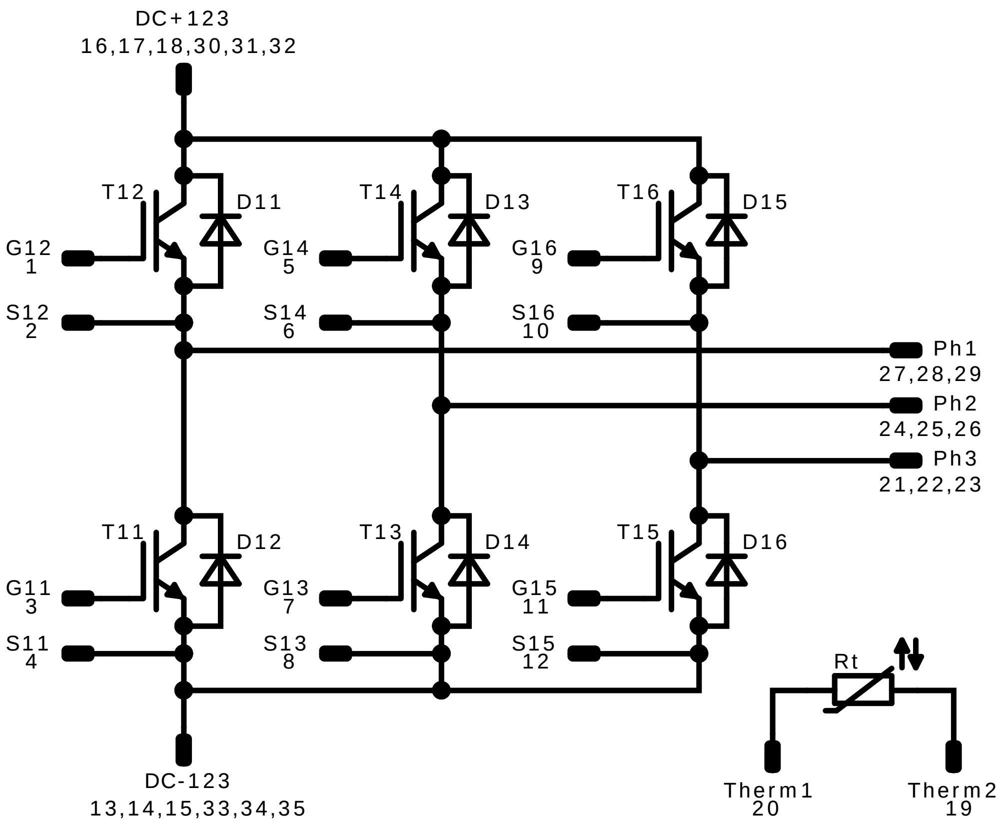
	**Text**	**Name**		**VIN**	**Date code**	**Lot**	**Serial**
		NN-NNNNNNNNNNNNNN-TTTTTTVV		VIN	WWYY	LLLLL	SSSS
	Datamatrix	**Type&Ver**	**Lot number**	**Serial**	**Date code**		
		TTTTTTTVV	LLLLL	SSSS	WWYY		

Outline

Pin table [mm]			
Pin	X	Y	Function
1	19,05	0	G12
2	22,86	0	S12
3	34,29	0	G11
4	38,1	0	S11
5	49,53	0	G14
6	53,34	0	S14
7	64,77	0	G13
8	68,58	0	S13
9	80,01	0	G16
10	83,82	0	S16
11	95,25	0	G15
12	99,06	0	S15
13	118,11	15,865	DC-123
14	118,11	19,675	DC-123
15	118,11	23,485	DC-123
16	118,11	34,915	DC+123
17	118,11	38,725	DC+123
18	118,11	42,535	DC+123
19	100,965	58,4	Therm1
20	97,155	58,4	Therm2
21	81,915	58,4	Ph3
22	78,105	58,4	Ph3
23	74,295	58,4	Ph3
24	59,055	58,4	Ph2
25	55,245	58,4	Ph2
26	51,435	58,4	Ph2
27	36,195	58,4	Ph1
28	32,385	58,4	Ph1
29	28,575	58,4	Ph1
30	0	42,535	DC+123
31	0	38,725	DC+123
32	0	34,915	DC+123
33	0	23,485	DC-123
34	0	19,675	DC-123
35	0	15,865	DC-123



Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T11, T12, T13, T14, T15, T16	IGBT	1200 V	150 A	Inverter Switch	
D11, D12, D13, D14, D15, D16	FWD	1200 V	150 A	Inverter Diode	
Rt	Thermistor			Thermistor	

Packaging instruction				
Standard packaging quantity (SPQ) 24	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for VINco E3 packages see vincotech.com website.

Package data
Package data for VINco E3 packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
A0-VS126PA150M7-L998F70-D3-14	26 Sep. 2021	All static and dynamic characteristics are updated Separated datasheet for solder pin version New datasheet format, module is unchanged	